Preliminary Product Information

MOS Integrated Circuit

78K0/KD2

8-BIT SINGLE-CHIP MICROCONTROLLER

The 78K0/KD2 products are 8-bit single-chip microcontrollers of the 78K0 series. These microcontrollers feature Single-voltage Self-programming Flash memory and many peripherals.

FEATURES

• 78K0 CPU core, 8-bit CISC architecture

 Flash EEPROM and RAM sizes 	
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lte	m Program memory	Data memory
Product name	(Flash EEPROM)	(RAM)
μPD78F0527	128K bytes (Flash)	7K bytes
μPD78F0526	96K bytes (Flash)	5K bytes
μPD78F0525	60K bytes (Flash)	3K bytes
μPD78F0524	48K bytes (Flash)	2K bytes
μPD78F0523	32K bytes (Flash)	1K bytes
μPD78F0522	24K bytes (Flash)	1K bytes
μPD78F0521	16K bytes (Flash)	768 bytes

Minimum instruction cycle

- 0.1µs (20MHz@4.0V to 5.5V)
- 0.2µs (10MHz@2.7V to 5.5V)
- $0.4 \mu s$ (5MHz@1.8V to 5.5V)

Clock

- MAIN CLOCK
 - Internal Ring-oscillator 8MHz (Typ.)
 - Ceramic/Crystal Oscillator/External CLK (2MHz to 20MHz) (Instruction execution time = 100ns(min.) @20MHz)
- SUB CLOCK
 - 32.768KHz Crystal oscillator/ External CLK
- WDT CLOCK
 - Internal Ring-oscillator 240KHz (Typ.)

Peripherals.

- On-Chip Power-On-Clear (POC) Circuit
- Low-Voltage Detector (LVI) Circuit
- Timer
 - 16bit Timer 1ch
 - 8bit Timer 4ch
 - Watch Timer
- Watchdog Timer (Operable with 240KHz Ring-OSC)
- Serial Interface
- UART/CSI 1ch
- UART (with LIN-bus) 1ch
- IIC 1ch

- Key Interrupt 8ch
- AD CONVERTER
- 10-bit resolution A/D converter 8ch
- I/O PORT
 - Total : 45
 - CMOS I/O : 40
 - CMOS Output: 1
 - . N-ch O.D I/O: 4
- •MULTUPLIER/DIVIDER
 - 16bit x 16bit, 32bit / 16bit
 - (µPD78F0524/0525/0526/0527 only)
- Other
 - Self programming ·
 - PCL OUTPUT
 - On-chip debug function (Product name is undecided)

Interrupt

- Internal 16ch
- External 8ch

Operation Voltage

1.8V to 5.5V

Package

52-pin LQFP(10mm x 10mm, 0.65mm pitch)

This information contained in this document is being issued in advance of the production cycle for the product. The parameters for the product may change before final production or NEC Electronics Corporation, at its own discretion,, may withdraw the product prior to its production. Not all products and/ or types are available in every country. Please check with an NEC Electronics sales representative for availability and additional information.

Data memory

1. Block Diagram



Fig. 78K0/KD2

* : μPD78F0527/0526/0525/0524 only

2. Pin Lay Out

78K0/KD2

52-pin plastic LQFP (10 x 10mm 0.65mm pitch) μ PD78F0527GB-UET, μ PD78F0526GB-UET, μ PD78F0525GB-UET, μ PD78F0524GB-UET, μ PD78F0523GB-UET, μ PD78F0522GB-UET, μ PD78F0521GB-UET



3. Pin Function

Table (1/2)

PIN NAME	Function
VDD	Positive power supply except for ports (except P20-P27) and AD converter
VSS	Ground potential except for ports (except P20-P27) and AD converter
RESET	System reset input
FLMD0	Flash EEPROM programming mode setting
REGC	Connecting regulator stabilization capacitor. Connect to ground via a
	capacitor (0.47 μ F)
AVREF	A/D converter analog power supply and power supply for P20-P27
AVSS	Ground potential for A/D converter and P20 - P27.
P00	I/O port
/TI00	External count clock input to 16-bit timer/event counter 00
	Capture trigger input to capture registers (CR000, CR010) of16-bit
	timer/event counter 00 (TM00)
P01	I/O port
/TI010	Capture trigger input to capture register (CR000) of 16-bit timer/event
/TO00	counter 00 (TM00)
	16-bit timer/event counter 00 output (TM00)
P02	I/O port
P03	I/O port
P10	I/O port
/SCK10	Clock input/ output for serial interface (CSI10)
/TXD0	Serial data output from asynchronous serial interface (UART0)
P11	I/O port
/SI10	Serial data input to serial interface (CSI10)
/RXD0	Serial data input to asynchronous serial interface (UART0)
P12	I/O port
/SO10	Serial data output form serial interface (CSI10)
P13	I/O port
/TXD6	Serial data output from asynchronous serial interface (UART6)
P14	I/O port
/RXD6	Serial data input from asynchronous serial interface (UART6)
P15	I/O port
/TOH0	8-bit timer H0 output (TMH0)
P16	I/O port
/TOH1	8-bit timer H1 output (TMH1)
/INTP5	External interrupt request input with specifiable valid edges
P17	I/O port
/TI50	External count clock input to 8-bit timer/event counter 50 (TM50)
/TO50	8-bit timer/event counter 50 output (TM50)
P20- P27	I/O ports
/ ANIO- ANI7	A/D converter analog input
P30/INTP1	I/O port
P31/INTP2	External interrupt request input with specifiable valid edges
P32/INTP3	
P33	I/O port
/TI51	External count clock input to 8-bit timer/event counter 51(TM51)
/1051	8-bit timer/event counter 51output (TM51)
/INTP4	External interrupt request input with specifiable valid edges
P40 - P41	I/O port

Table()	2/2)
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PIN NAME	Function
P60	I/O port (N-ch Open drain)
/SCL0	Clock input/ output for serial interface (IIC0)
P61	I/O port (N-ch Open drain)
/SDA0	Serial data input/ output for serial interface (IIC0)
P62	I/O port (N-ch Open drain)
/EXSCL0	External clock input for serial interface (IIC0)
P63	I/O port (N-ch Open drain)
P70 – P77	I/O ports
/KR0 – KR7	Key interrupt input
P120	I/O port
/INTP0	External interrupt request input with specifiable valid edges
/EXLVI	Reference voltage input for Low voltage Indicator
P121	I/O port (An external oscillation circuit is not used)
/X1	Connecting resonator for main system clock oscillation
P122	I/O port (An external oscillation circuit is not used)
/X2	Connecting resonator for main system clock oscillation
/EXCLK	External clock input for main system clock
P123	I/O port (An external oscillation circuit is not used)
/XT1	Connecting resonator for subsystem clock oscillation
P124	I/O port (An external oscillation circuit is not used)
/XT2	Connecting resonator for subsystem clock oscillation
/EXCLKS	External clock input for subsystem clock
P130	Output port
P140	I/O port
/PCL	Clock output
/INTP6	External interrupt request input with specifiable valid edge

4. Memory space

78K0/KD2 have 64kB linear address area.

To access more than 64KB ROM area, 96KB and 128KB ROM products have BANK type ROM at address of 8000H to C000H. All BANK ROM size is 16KB.

		Common ROM	Bank R	Bank ROM	
Products ROM size		Address	Address	Number of Bank	
μPD78F0527	128KB	0000H-7FFFH (32KB)	8000H-BFFFH (16KB)	6	
μPD78F0526	96KB	0000H-7FFFH (32KB)	8000H-BFFFH (16KB)	4	
μPD78F0525	60KB	0000H-EFFFH (60KB)	-	-	
μPD78F0524	48KB	0000H-BFFFH (48KB)	-	-	
μPD78F0523	32KB	0000H-7FFFH (32KB)	-	-	
μPD78F0522	24KB	0000H-5FFFH (24KB)	-	-	
μPD78F0521	16KB	0000H-3FFFH (16KB)	-	-	

5. Clock

78K0/KD2 have 2 type internal Ring-OSC and 2 type external resonator oscillation circuit. 78K0/KD2 can be operated high-speed internal Ring-OSC only. Low-speed Ring-OSC can connect to Watch dog timer and 8bit timer (TMH1) only for high secure.



Fig. Clock connecting block image

6. Outline of Functions of KD2

		μPD78F0521	μ PD78F0522	μPD78F0523		
Internal	Flash Memory	16 K	24 K	32 K		
Memory	Bank		_			
(Byte)						
	High Speed RAM	768		IK		
	Extend RAM		-			
Main System	Ceramic/Crystal	- 2 to 20 MHz: V _{DD} = 4.0 to 5.5 \	1			
Clock		- 2 to 10 MHz: VDD = 2.7 to 5.5 \	/			
		- 2 to 5 MHz: VDD = 1.8 to 5.5 V				
	Internal Ring-OSC	- 8 MHz(TYP.)				
Sub System Clo	ock	- 32.768 kHz(TYP.)				
Internal Low Sp	eed Ring-OSC	- 240 kHz(TYP.)				
(For TMH1, WD	DT)					
Minimum Instruc	ction Cycle	- 0.1 µ s (Ceramic/ Crystal O	peration fxH = 20 MHz VDD = 4.0) to 5.5 V)		
I/O		Total	:45			
		- CMOS I/O	:40			
		- CMOS Out	:1			
		- N-ch O.D.	:4			
Timer		- 16 Bit Timer/Event Counter:1ch				
		- 8 Bit Timer/Event Counter:2ch				
		- 8 bit Timer:2ch				
		- Watch Timer:1ch				
		- Watch Dog Timer:1ch				
	Timer Output	-5(PWM:3)				
PCL output		- 156.25kHz, 312.5kHz, 615kHz, 1.25MHz, 2.5MHz, 5MHz, 10MHz (fprs = 20 MHz)				
Buzzer Output			-			
A/D Converter		- 10bit x 8ch				
Serial Interface		- UART (with LIN-bus):1ch				
		- CSI/ UART:1ch				
		- I ² C:1ch				
Multiplier/Divide	er		-			
Interrupt	Internal	16				
	External	8				
Key Return		8ch				
On Chip Debug Function		Product name is undecided.				
Voltage Range		V _{DD} = 1.8 to 5.5 V				
Operation temp	erature	Ta = -40°C to +85°C				
Package		- 52pin LQFP(10x10) 0.65mm p	itch			

		μPD78F0524	μPD78F0525	μPD78F0526	μPD78F0527			
Internal	Flash Memory	48 K	60 K	96 K	128 K			
Memory (Byte)	Bank	-	-	4	6			
	High Speed RAM		I					
	Extend RAM	1 K	2 K	4 K	6 K			
Main System	Ceramic/Crystal	- 2 to 20 MHz: VDD = 4.0) to 5.5 V					
Clock		-2 to 10 MHz: VDD = 2.7 to 5.5 V						
		- 2 to 5 MHz: VDD = 1.8	to 5.5 V					
	Internal Ring-OSC	- 8 MHz(TYP.)						
Sub System Clo	ock	- 32.768 kHz(TYP.)						
Internal Low Sp	eed Ring-OSC	- 240 kHz(TYP.)						
(For TMH1, WD	DT)							
Minimum Instruc	ction Cycle	- 0.1 μ s (Ceramic/ Cr	ystal Operation $f_{XH} = 20$	MHz VDD = 4.0 to 5.5 V)			
I/O		Total	:45					
		- CMOS I/O :40						
		- CMOS Out :1						
Timer		- 16 Bit Timer/Event Counter:1ch						
		- 8 Bit Timer/Event Counter:2ch						
		- 8 bit Timer:2ch						
		- Watch Timer:1ch						
		- Watch Dog Timer:1ch						
	Timer Output	-5(PWM:3)						
PCL output		- 156.25kHz, 312.5kHz, 615kHz, 1.25MHz, 2.5MHz, 5MHz, 10MHz (fprs = 20 MHz)						
Buzzer Output				-				
A/D Converter		- 10bit x 8ch						
Serial Interface		- UART (with LIN-bus):1ch						
		- CSI/ UART:1ch						
		- 1 ² C:1ch						
Multiplier/Divide	er	16bitx16bit, 32bit/8bit						
Interrupt	Internal	16						
	External	8						
Key Return		8ch						
On Chip Debug	Function	Product name is undecided.						
Voltage Range		V _{DD} = 1.8 to 5.5 V						
Operation temp	erature	$Ta = -40^{\circ}C \text{ to } +85^{\circ}C$						
Package		- 52pin LQFP(10x10) 0.65mm pitch						

7. Electrical specification of KD2 (Target)

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Caution These specifications show target values, which may change after device evaluation. The operating voltage range may also change.

Parameter	Symbol		Conditions	Ratings	Unit
Supply voltage	Vdd			-0.5 to +6.5	V
	Vss			-0.5 to +0.3	V
	AVREF			-0.5 to +6.5	V
	AVss			-0.5 to +0.3	V
Input voltage	VI1	1		-0.3 to V _{DD} +0.3 ^{Note}	V
	Vı2	P60-P63(N-ch open drain)	-0.3 to +6.5	V
Output voltage	Vo			-0.3 to V _{DD} +0.3 ^{Note}	V
Analog input voltage	Van			-0.3 to AV _{REF} +0.3 ^{Note}	V
Output current, high	Іон	Per pin		-10	mA
		Total of	P00-P03, P40-P41,	-25	mA
		all pins	P120-P124, P130, P140		
		-80 mA	P10-P17,P30-P33,	-55	mA
			P60-P63, P70-P77		

Absolute Maximum Ratings($T_A = 25^{\circ}C$) (1/2)

Note Must be 6.5 V or lower.

- **Caution** Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of port pins.

Absolute Maximum Ratings($T_A = 25^{\circ}C$) (2/2)

Parameter	Symbol	Conditions		Ratings	Unit
Output current, low	lo∟	Per pin		30	mA
		Total of all	P00-P03, P40-P41,	60	mA
		pins	P120-P124, P130, P140		
		200 mA	P10-P17,P30-P33,	140	mA
			P60-P63, P70-P77		
Operating	TA	In normal op	peration mode	-40 to +85	°C
ambient temperature		In flash men	nory programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

High-Speed System Clock	(Crystal/Ceramic) Oscillator	Characteristics
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		4 0 1 4 1 4 5 5 5 5 5		
($I_{A} = -40 \text{ to } +85^{\circ}\text{C}$	18V <vnv<55v< td=""><td>$23V \leq AV_{RFF} \leq V_{DD}$</td><td>$V_{SS} = AV_{SS} = () V$</td></vnv<55v<>	$23V \leq AV_{RFF} \leq V_{DD}$	$V_{SS} = AV_{SS} = () V$
١.	1 = 10.00 + 00 = 0			, v 0 0 - 1 v 0 0 - 0 v

Resonator	Recommended Circuit	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Ceramic resonator	V _{ss} X1 X2 C1+ C2+	Oscillation frequency(fxH) ^{Note}	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V \\ \\ 2.7 \ V \leq V_{DD} < 4.0 \ V \\ \\ 1.8 \ V \leq V_{DD} < 2.7 \ V \end{array}$	2.0 2.0 2.0		20.0 10.0 5.0	MHz
Crystal resonator	V _{SS} X1 X2 C1= C2=	Oscillation frequency(fxH) ^{Note}	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V \\ \\ 2.7 \ V \leq V_{DD} < 4.0 \ V \\ \\ 1.8 \ V \leq V_{DD} < 2.7 \ V \end{array}$	2.0 2.0 2.0		20.0 10.0 5.0	MHz



- **Cautions 1.** When using the high-speed system clock oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.
 - Keep the wiring length as short as possible.
 - Do not cross the wiring with the other signal lines.
 - Do not route the wiring near a signal line through which a high fluctuating current flows.
 - Always make the ground point of the oscillator capacitor the same potential as Vss.
 - Do not ground the capacitor to a ground pattern through which a high current flows.
 - Do not fetch signals from the oscillator.
 - 2. Since the CPU is started by the Ring-OSC after reset is released, check the oscillation stabilization time of the high-speed system clock using the oscillation stabilization time status register (OSTC). Determine the oscillation stabilization time of the OSTC register and oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- **Remark** For the resonator selection and oscillator constant, customers are requested to either evaluate the oscillation themselves or apply to the resonator manufacturer for evaluation.

Ring-OSC Oscillator Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}, 2.3 \text{ V} \le \text{AVREF} \le \text{Vdd}, \text{Vss} = \text{AVss} = 0 \text{ V})$

Resonator	Parameter	Conditions	MIN.	TYP.	MAX.	Unit				
8 MHz Ring-OSC oscillator	Ring-OSC oscillator High-speed Ring-OSC Oscillation		7.6 Note2	8.0 Note2	8.4 Note2	MHz				
	frequency(fRH) ^{Note1}	$1.8~V \le V_{\text{DD}} \le 5.5~V$	T.B.D	8.0 Note2	T.B.D	MHz				
240 kHz Ring-OSC oscillator	Low-speed Ring-OSC	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	216	240	264	kHz				
	Oscillation frequency(fRL)	$1.8~V \leq V_{\text{DD}} \leq 5.5~V$	T.B.D	240	T.B.D	kHz				

Note 1. Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.

 This is the frequency in the case of RSTS(RCM.7)=1. This is 5 MHz(TYP.) in the case of RSTS=0.

Subsystem Clock Oscillator Characteristics

(TA = -40 to +85°C, 1.8 V \leq VDD \leq 5.5 V, 2.3 V \leq AVREF \leq VDD, VSS = AVSS = 0 V)

Resonator	Recommended	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
	Circuit						
Crystal resonator		Oscillation		32	32.768	35	kHz
	V _{ss} XT2 XT1 Rd C4 C3 7 777	frequency(fs∪в) ^{Note}					

Note Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.

- **Cautions 1.** When using the subsystem clock oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.
 - Keep the wiring length as short as possible.
 - Do not cross the wiring with the other signal lines.
 - Do not route the wiring near a signal line through which a high fluctuating current flows.
 - Always make the ground point of the oscillator capacitor the same potential as Vss.
 - Do not ground the capacitor to a ground pattern through which a high current flows.
 - 2. The subsystem clock oscillator is designed as a low-amplitude circuit for reducing power consumption, and is more prone to malfunction due to noise than the high-speed system clock oscillator. Particular care is therefore required with the wiring method when the subsystem clock is used.
- **Remark** For the resonator selection and oscillator constant, customers are requested to either evaluate the oscillation themselves or apply to the resonator manufacturer for evaluation.

DC Characteristics (1/4)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = \text{AV}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high	Іон1	Per pin of P00-P03, P10-P17,	$4.0V \le V_{\text{DD}} \le 5.5V$			-3.0	mA
		P30-P33, P40-P41, P70-P77, P120,	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{V}$			-2.5	
		P130, P140	$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{V}$			-1.0	
		Total of P00-P03, P40-P41, P120,	$4.0V \leq V_{\text{DD}} \leq 5.5V$			-20.0	mA
		P130, P140	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{V}$			-10.0	
			$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{V}$			-5.0	
		Total of P10-P17, P30-P33, P70-P77	$4.0V \le V_{\text{DD}} \le 5.5V$			-30.0	mA
			$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{V}$			-19.0	
			$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{V}$			-10.0	
		Total of all pins	$4.0V \le V_{\text{DD}} \le 5.5V$			-50.0	mA
			$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{V}$			-29.0	
			$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{V}$			-15.0	
	Іон2	Per pin of P20-P27, P121-P124 Note	$1.8~V \le V_{\text{DD}} \le 5.5V$			-100	μA
Output current, low	IOL1	Per pin of P00-P03, P10-P17,	$4.0V \le V_{\text{DD}} \le 5.5V$			8.5	mA
Output current, low		P30-P33, P40-P41, P70-P77, P120,	$2.7~V \leq V_{\text{DD}} < 4.0V$			5.0	
		P130, P140	$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{V}$			2.0	
		Per pin of P60-P63 4	$4.0V \le V_{\text{DD}} \le 5.5V$			15.0	mA
			$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{V}$			5.0	
			$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{V}$			2.0	
		Total of P00-P03, P40-P41, P120,	$4.0V \le V_{\text{DD}} \le 5.5V$			20.0	mA
		P130, P140	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{V}$			15.0	
			$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{V}$			9.0	
		Total of P10-P17, P30-P33,	$4.0V \le V_{\text{DD}} \le 5.5V$			45.0	mA
		P70-P77	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{V}$			35.0	
			$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{V}$			20.0	
		Total of all pins	$1.8~V \le V_{\text{DD}} \le 5.5V$			65.0	mA
			$4.0V \le V_{\text{DD}} \le 5.5V$			50.0	
			$2.7~V \le V_{\text{DD}} < 4.0V$			29.0	
	IOL2	Per pin of P20-P27 Note	$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{V}$			400	μA

Note When used as digital input ports, set $AV_{REF} = V_{DD}$.

Caution This specification is Duty = 70% condition of IOH and IOL.

DC Characteristics (2/4)

$(T_A = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = AV_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P02, P12, P13, P15, P40-P41, P60-P63, P121-P124	0.7Vdd		Vdd	V
	V _{IH2}	P00, P01, P03 P10-P11, P14, P16-P17, P30-P33, P70-P77, P120, P140, RESET	0.8Vdd		Vdd	V
	Vінз	P20-P27 ^{Note}	0.7AV _{REF}		AVREF	V
Input voltage, low	VIL1	P02, P12, P13, P15, P40-P41, P60-P63, P121-P124,	0		0.3Vdd	V
	VIL2	P00, P01, P03 P10-P11, P14, P16-P17, P30-P33,	0		0.2V _{DD}	V
		P70-P77, P120, P140, RESET				
	VIL3	P20-P27 ^{Note}	0		$0.3AV_{REF}$	V

Note When used as digital input ports, set $AV_{REF} = V_{DD}$.

DC Characteristics (3/4)

$(T_A = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = AV_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions	Conditions			MAX.	Unit
Output voltage, high	Voh1	lон = -3.0 mA	P00-P03, P10-P17, P30-P33, P40-P41,	$4.0V \le V_{\text{DD}} \le 5.5V$	Vdd-0.7			V
		lон = -2.5 mA	P70-P77, P120, P130, P140	$2.7~V \le V_{\text{DD}} \le 5.5V$	Vdd-0.5			V
		Іон = -1.0 mA		$1.8~V \le V_{\text{DD}} \le 5.5V$	Vdd-0.5			V
	Vон2	Іон = -100 μА	P20-P27	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$ $\text{AV}_{\text{REF}} = \text{V}_{\text{DD}}$	Vdd-0.5			V
Output voltage, low	Vol1	lo∟ = 8.5 mA	P00-P03, P10-P17, P30-P33, P40-P41,	$4.0V \leq V_{\text{DD}} \leq 5.5V$			0.7	V
		lo∟ = 1.0 mA	P70-P77, P120, P130, P140	$2.7~V \le V_{\text{DD}} \le 5.5V$			0.5	V
		loL = 0.5 mA		$1.8~V \le V_{\text{DD}} \le 5.5V$			0.4	V
	Vol2	lol = 400 μA	P20-P27	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$ $\text{AV}_{\text{REF}} = \text{V}_{\text{DD}}$			0.4	V
	Vol3	lo∟ = 15.0 mA	P60-P63	$4.0V \le V_{\text{DD}} \le 5.5V$			2.0	V
		loL = 5.0 mA]				0.4	V
	loL = 3.0 mA		$2.7~V \leq V_{\text{DD}} \leq 5.5V$			0.4	V	
		lo∟ = 2.0 mA		$1.8~V \le V_{\text{DD}} \le 5.5V$			0.4	V
Input leakage	Ішні	Vi = Vdd	P00-P03, P10-P17, P30- P120-P124, P130, P140	P33, P40-P41, P70-P77,			1	μA
current, nigh	ILIH2	$V_{\text{I}} = AV_{\text{REF}}$	P20-P27				1	μA
	Ішнз	$V_I = V_{DD}$	X1, X2, XT1, XT2 (When use External	X1, X2, XT1, XT2 (When use External oscillator)			20	μA
Input leakage current, low	Ilili	VI = Vss	P00-P03, P10-P17, P30 P120-P124, P130, P140	-P33, P40-P41, P70-P77,			-1	μA
	Ilil2	$V_{I} = AV_{REF}$	P20-P27				-1	μA
	Ililis	Vi = Vss	X1, X2, XT1, XT2 (When use External	oscillator)			-20	μA
Pull-up resistance value	Ru	$V_{I} = V_{DD}$	1		10	20	100	kΩ
FLMD0 supply	VIL	In normal opera	tion mode		0		0.2Vdd	V
voltage	Vін	In flash memory	programming mode		0.8Vdd		Vdd	V

DC Characteristics (4/4)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}\text{DD} \le 5.5 \text{ V}, 2.3 \text{ V} \le \text{AV}\text{REF} \le \text{V}\text{DD}, \text{V}\text{SS} = \text{AV}\text{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operation mode	$f_{XH} = 20 \text{ MHz}^{\text{Note2}}, \text{ V}_{DD} = 5.0 \text{ V}$		4.7	5.8	mA
current ^{Note1}			$f_{XH} = 10 \text{ MHz}^{\text{Note}^2}, \text{ V}_{DD} = 5.0 \text{ V}^{\text{Note}^3}$		2.5	3.5	mA
			$f_{XH} = 5 \text{ MHz}^{\text{Note}^2}, \text{ V}_{DD} = 3.0 \text{ V}^{\text{Note}^3}$		1.5	2.2	mA
			$f_{RH} = 8 \text{ MHz}^{\text{Note2}}, \text{ V}_{DD} = 5.0 \text{ V}$		1.9	2.7	mA
			$f_{SUB} = 32.768 \text{ kHz}^{\text{Note}2}, \text{V}_{DD} = 5.0 \text{ V}$		17	T.B.D.	μA
	IDD2 HALT mode	HALT mode	fxH = 20 MHz ^{Note2} , V _{DD} = 5.0 V		2.2	2.6	mA
			$f_{XH} = 10 \text{ MHz}^{\text{Note2}}, V_{DD} = 5.0 \text{ V}^{\text{Note3}}$		1.0	1.2	mA
			$f_{XH} = 5 \text{ MHz}^{\text{Note2}}, V_{DD} = 3.0 \text{ V}^{\text{Note3}}$		0.55	0.65	mA
			$f_{RH} = 8 \text{ MHz}^{\text{Note2}}, \text{ V}_{DD} = 5.0 \text{ V}$		0.6	0.65	mA
			$f_{SUB} = 32.768 \text{ kHz}^{\text{Note2}}, \text{V}_{DD} = 5.0 \text{ V}$		3.5	T.B.D.	μA
	IDD3	STOP mode	V _{DD} = 5.0 V		1	20	μA
	IADC	A/D converter	A/D converter operating		0.57	1.3	mA
		operating current	A/D converter not operating		T.B.D.	T.B.D.	mA
	Iwdt	Watchdog Time	240 kHz Ring-OSC operating		5	10	μA
		operating current					·
	Ilvi	LVI operating			9	T.B.D.	μA
		current					

Notes 1. Total current flowing through the internal power supply (V_{DD}) .

2. Input square-wave

3. When AMPH(OSCCTL.0) = 0.

Remark 1. fxH: High-Speed System Clock oscillation frequency (X1 clock oscillation frequency or External main system clock frequency).

- 2. fRH: High-speed Ring-OSC oscillation frequency.
- **3.** fsub: Subsystem Clock oscillation frequency (XT1 clock oscillation frequency or External subsystem clock frequency).

AC Characteristics

(1)Basic operation

(TA = -40 to +85°C, 1.8 V \leq VDD \leq 5.5 V, 2.3 V \leq AVREF \leq VDD, VSS = AVSS = 0 V)

Parameter	Symbol		Conditi	ons	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсү	Main	High-speed	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	0.1		16	μs
instruction execution time)		system	system	$2.7~V \leq V_{\text{DD}} < 4.0~V$	0.2		16	μs
		clock(fxp)	clock(fxH)	$1.8~V \leq V_{\text{DD}} < 2.7~V$	0.4		16	μs
		operation						
			High-speed	$2.7~V \leq V_{\text{DD}} < 5.5~V$	0.25		4	μs
			Ring-OSC	$1.8~V \leq V_{\text{DD}} < 2.7~V$	0.5		4	μs
			clock(free)					
		Subsystem	n clock(fsuB)opera	ation	114	122	125	μs
External main system clock	fexclk	$4.0 \ V \leq V_{DI}$	o≤5.5 V		2.0		20.0	MHz
frequency		$2.7 \ V \le V_{DI}$	o < 4.0 V		2.0		10.0	MHz
		$1.8 \text{ V} \leq \text{V}_{\text{DI}}$	o < 2.7 V		2.0		5.0	MHz
External main system clock	texclкн,				(1/ fexclk			ns
input high-/low-level width	t exclkl			x 1/2) - 1				
External subsystem clock	fexclks				32	32.768	35	kHz
frequency								
External subsystem clock	texclksh,				(1/ fexcliks			ns
input high-/low-level width	t EXCLKSL				x 1/2) - 5			
TI000, TI010 input high-level	t⊤iнo,	$4.0 \ V \leq V_{DI}$	o≤5.5 V		2/fsam+			μs
width, low-level width	t⊤ilo				0.1 Note1			
		$2.7 \text{ V} \leq V_{DI}$	o < 4.0 V		2/fsam+			μs
					0.2 Note1			
TI50, TI51 input frequency	fтıs	$4.0 \ V \leq V_{DI}$	o≤5.5 V				10	MHz
		$2.7 \text{ V} \leq V_{DI}$	o < 4.0 V				10	MHz
		$1.8 \text{ V} \leq \text{V}_{DI}$	o < 2.7 V				5	MHz
TI50, TI51 input high-level	t⊤⊪s,	$4.0 \ V \leq V_{DI}$	o≤5.5 V		50			ns
width, low-level width	ttil5	$2.7 \text{ V} \leq V_{DI}$	o < 4.0 V		50			ns
		$1.8 \text{ V} \leq \text{V}_{DI}$	o < 2.7 V		100			ns
Interrupt input high-level	tınтн,				1			μS
width, low-level width	tintl							
Key return input low-level	t KR				250			ns
width								
RESET low-level width	trsl				10 Note2			μs

Notes 1. Selection of f_{sam} = f_{PRS}, f_{PRS} /4, f_{PRS} /256 is possible using bits 0 and 1 (PRM000, PRM001) of prescaler mode register (PRM00). Note that when selecting the TI000 valid edge as the count clock, f_{sam} = f_{PRS}.

2. Input low level signal into RESET pin until power supply voltage is stabilized in the case of the power supply voltage rise time is slowly (more than 3.4ms).



Remark The values indicated by the shaded section are only when the High-speed Ring-OSC clock is selected.

AC Timing Test Points (Excluding X1 Input)



(2) Serial interface

(TA = -40 to +85°C, 1.8 V \leq VDD \leq 5.5 V, 2.3 V \leq AVREF \leq VDD, VSS = AVSS = 0 V)

(a)UART mode (UART6, dedicated baud rate generator output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					312.5	kbps

(b) UART mode (UART0, dedicated baud rate generator output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					312.5	kbps

(c) IIC0 mode

Parameter	Symbol	Norma	l mode	High spe	ed mode	Unit
		MIN.	. MAX	MIN.	. MAX	
SCL0 clock frequency	fclk	0	100	0	400	kHz
Start/restart condition setup time ^{Note1}	tsu: sta	4.8	-	0.7	-	μs
hold time	t hd: sta	4.1	-	0.7	-	μs
Hold time in SCL = "L"	tLOW	5.0	-	1.25	-	μs
Hold time in SCL = "H"	tніgн	5.0	-	1.25	-	μs
Data setup time (reception)	tsu: dat	0	-	0	-	μs
Data hold time (sending) ^{Note2}	thd: dat	0.47	4.0	0.23	1.00	μs

Notes 1. The first clock pulse is generated after this period in the case of the start/restart condition.
 2. The MAX of the transition value. Wait is occurred in the term of ACK(acknowledge).

Caution Specification at 1.8 V \leq V_{DD} < 2.7V is not fixed.

(d) 3-wire serial I/O mode (CSI10 master mode, SCK1n...internal clock output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK1n cycle time	tKCY1	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	100			ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$	200			ns
SCK1n high-/low-level width	tкнı,		tkcy1/2 - 10 ^{Not1}			ns
	t ĸ∟1					
SI1n setup time (to SCK1n↑)	tsik1		30			ns
SI10hold time (to SCK1n↑)	tksi1		30			ns
Delay time from $\overline{SCK1n}\downarrow$ to SO1n	tkso1	C = 50 pF ^{Note2}			40	ns
output						

Notes 1. This is the value when the high<u>-speed</u> system clock (f_{XH}) is operating.

2. C is the load capacitance of the SCK1n and SO1n output lines.

(e) 3-wire serial I/O mode (CSI10 slave mode, SCK1n...external clock input)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK1n cycle time	t ксү2		400			ns
SCK1n high-/low-level width	tкн2,		T.B.D			ns
	tĸ∟2					
SI1n setup time (to SCK1n↑)	tsik2		80			ns
SI1n hold time (to SCK1n↑)	tksi2		50			ns
Delay time from $\overline{\text{SCK1n}\downarrow}$ to SO1n	tĸso2	$C = 50 \text{ pF}^{Note}$			120	ns
output						

Note C is the load capacitance of the SO1n output lines.

Remark n = 0

Caution Specification at 1.8 V \leq V_{DD} < 2.7V is not fixed.

Serial Transfer Timing

3-wire serial I/O mode:





A/D Converter Characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	Res				10	bit
Overall error Note1,2	AINL	$4.0 \text{ V} \leq AV_{\text{REF}} \leq 5.5 \text{ V}$			±0.4	%FSR
		$2.7 \text{ V} \leq AV_{\text{REF}} \leq 5.5 \text{ V}$			±0.6	%FSR
		AVref < 2.7 V			T.B.D.	%FSR
Conversion time	tсолу	$4.0~V \leq AV_{\text{REF}} \leq 5.5~V$	6.6		30	μS
		$2.7~V \leq AV_{\text{REF}} \leq 5.5~V$	6.6		30	μS
		AVref < 2.7 V	11		T.B.D.	μS
Zero-scale error ^{Note1,2}	Ezs	$4.0~V \leq AV_{\text{REF}} \leq 5.5~V$			±0.4	%FSR
		$2.7 \text{ V} \leq AV_{\text{REF}} \leq 5.5 \text{ V}$			±0.6	%FSR
		AVref < 2.7 V			T.B.D.	%FSR
Full-scale error Note1,2	Efs	$4.0 \text{ V} \leq AV_{\text{REF}} \leq 5.5 \text{ V}$			±0.4	%FSR
		$2.7 \text{ V} \leq AV_{\text{REF}} \leq 5.5 \text{ V}$			±0.6	%FSR
		AVref <2.7 V			T.B.D.	%FSR
Integral linearity error Note1	ILE	$4.0 \text{ V} \leq \text{AV}_{\text{REF}} \leq 5.5 \text{ V}$			±2.5	LSB
		$2.7 \text{ V} \leq AV_{\text{REF}} \leq 5.5 \text{ V}$			±4.5	LSB
		AVref < 2.7 V			T.B.D.	LSB
Differential linearity error Note1	DLE	$4.0~V \leq AV_{\text{REF}} \leq 5.5~V$			±1.5	LSB
		$2.7~V \leq AV_{\text{REF}} \leq 5.5~V$			±2.0	LSB
		AVref < 2.7 V			T.B.D.	%FSR
Analog input voltage	VAIN		AVss		AVREF	V

		$A \cap (A \cap A) = A \cap (A \cap A) = $	\ \ / \
- ($1A = -4010 + 85^{\circ}$		1 1 1
		$101 \pm 100 \pm 0.01$, 2101 ± 100 , 100 ± 100 , 100 ± 100	•••

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

POC Circuit Characteristics (T_A = -40 to +85°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOC		1.3	1.5	1.7	V
Power supply rise time	tртн	VDD : VPOC \rightarrow 1.8 V (MIN. value of VDD)		75	T.B.D	mV/ms
Minimum pulse width	tew		T.B.D.	50		μs

Notes 1. When voltage rises, time required from detection to reset release

2. When voltage drops, time required from detection to reset occur.

POC Circuit Timing



I	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage	VLVIO		4.10	4.20	4.30	V
voltage	level	VLVI1		3.95	4.05	4.15	V
		VLVI2		3.81	3.91	4.01	V
		VLVI3		3.66	3.76	3.86	V
		VLVI4		3.51	3.61	3.71	V
		VLVI5		3.37	3.47	3.57	V
		VLVI6		3.22	3.32	3.42	V
		VLVI7		3.07	3.17	3.27	V
	V	VLVI8		2.93	3.03	3.13	V
		Vlvi9		2.78	2.88	2.98	V
		VLVI10		2.63	2.73	2.83	V
		VLVI11		2.49	2.59	2.69	V
		VLVI12		2.34	2.44	2.54	V
		VLVI13		2.19	2.29	2.39	V
		VLVI14		2.05	2.15	2.25	V
		VLVI15		1.90	2.00	2.10	V
	External input pin Note1	EXLVI	EXLVI < Vdd		1.21		V
Minimum p	oulse width	t∟w		T.B.D.	50		μS
Operation : time ^{Note2}	stabilization wait	TLWAIT1			10	T.B.D	μS

LVI Circuit Characteristics ($T_A = -40$ to $+85^{\circ}C$)

Note 1. Using EXLVI/P120/INTP0 pin

2. Time required from setting LVION to 1 to operation stabilization

Remark $V_{LVI(n-1)} > V_{LVIn} : n = 1-15$

LVI Circuit Timing



Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics (T_A = -40 to +85°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	Vdddr		1.3 ^{Note}		5.5	V

Note Dependence on POC detection voltage. The data is held before POC reset, but is not held after POC reset when voltage drops.



Flash Memory Programming Characteristics

(TA = -40 to +85°C, 2.3 V \leq Vdd \leq 5.5 V, 2.3 V \leq AVREF \leq Vdd, Vss = AVss = 0 V)

(1) Basic characteristics

Para	meter	Symbol	Conditions	MIN. TYP. MAX.		Unit	
VDD supply volta	age	Idd	f _{XP} = 10 MHz (TYP.), 20 MHz (MAX.) 4.5 11.0		mA		
Erase time ^{Note1}	Chip unit	Teraca			20	T.B.D	ms
	Sector unit	Terasa			20	T.B.D	ms
Write time		Twrwa			50.	T.B.D.	μS
Number of rewr	ites per chip	Cerwr	1 erase + 1 write after erase = 1 rewrite ^{Note2}	100		time	

Notes 1. The prewrite time before erasure and the erase verify time (writeback time) are not included.

2. When a product is first written after shipment, "erase → write" and "write only" are both taken as one rewrite.

(2) Serial write operation characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time from RESET↑ to FLMD0 count	TRFCF		T.B.D	10	T.B.D	ms
start						
Count execution time	TCOUNT		T.B.D	10	T.B.D	ms
FLMD0 counter high-/low-level width	Тсн/Тс∟		Tc x 0.45			μs
FLMD0 counter rise/fall time	Tr/Tf		12.5			μS

Remark These values may change after evaluation.

Serial Write Operation



• NOTES FOR CMOS DEVICES —

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (MAX) and V_{IH} (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (MAX) and V_{IH} (MIN).

(2) HANDLING OF UNUSED INPUT PINS

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to Vob or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

③ PRECAUTION AGAINST ESD

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

④ STATUS BEFORE INITIALIZATION

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

5 POWER ON/OFF SEQUENCE

In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current.

The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

6 INPUT OF SIGNAL DURING POWER OFF STATE

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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